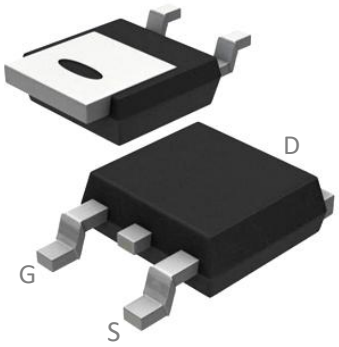
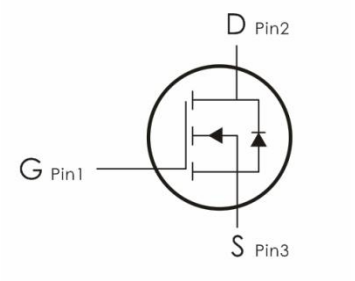
Description：

This N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.





Features：

1) V_{DS}=30V,I_D=25A,$R_{DS(ON)}$<25m Ω @V_{GS}=10V
2) Low gate charge.
3) Green device available.
4) Advanced high cell denity trench technology for ultra low $R_{DS(ON)}$.
5) Excellent package for good heat dissipation.

Absolute Maximum Ratings： (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain Current-T_C=25℃	25	A
	Continuous Drain Current-T_C=100℃	15	
	Continuous Drain Current-T_A=25℃	7.3	
	Continuous Drain Current-T_A=70℃	5.8	
I_{DM}	Pulsed Drain Current[2]	50	A
E_{AS}	Single Pulse Avalanche Energy[3]	8.1	mJ
I_{AS}	Avalanche Current	12.7	A
P_D	Power Dissipation[4], T_C=25℃	20.8	W
	Power Dissipation[4], T_A=25℃	2	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	℃

Thermal Characteristics：

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance,Junction to Case[1]	6	℃/W
$R_{\theta JA}$	Thermal Resistance Junction to mbient[1]	62	

Electrical Characteristics： (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Sourtce Breakdown Voltage	V_{GS}=0V,I_D=250μA	30	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS}=0V, V_{DS}=24V,T_A=25℃	---	---	1	μA
		V_{GS}=0V, V_{DS}=24V,T_A=55℃	---	---	5	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±30V, V_{DS}=0A	---	---	±100	nA
On Characteristics						
$V_{GS(th)}$	GATE-Source Threshold Voltage	V_{GS}=V_{DS}, I_D=250μA	0.5	0.9	1.3	V
$R_{DS(ON)}$	Drain-Source On Resistance[2]	V_{GS}=10V,I_D=10A	---	---	25	mΩ
		V_{GS}=4.5V,I_D=8A	---	---	28	mΩ
G_{FS}	Forward Transconductance	V_{DS}=5V , I_D=10A	---	5.5	---	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=15V, V_{GS}=0V, f=1MHz	---	410	---	pF
C_{oss}	Output Capacitance		---	60	---	
C_{rss}	Reverse Transfer Capacitance		---	50	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD}=15V,I_D=10A, R_G=3.3Ω,V_{GS}=10V	---	1.6	---	ns
t_r	Rise Time		---	15.8	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	13	---	ns

t_f	Fall Time		---	4.8	---	ns
Q_g	Total Gate Charge	V_{GS}=4.5V, V_{DS}=15V, I_D=10A	---	4.9	---	nC
Q_{gs}	Gate-Source Charge		---	1.66	---	nC
Q_{gd}	Gate-Drain "Miller" Charge		---	1.85	---	nC
R_G	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	2.3	---	Ω
Drain-Source Diode Characteristics						
I_S	Max. Diode Forward Current[1,5]	V_G=V_D=0V , Force Current	---	---	24	A
I_{SM}	Max. Pulsed Forward Current[2,5]		---	---	50	A
V_{SD}	Source-Drain Diode Forward Voltage[2]	V_{GS}=0V, I_S=1A ,T_J=25℃	---	---	1.2	V
trr	Reverse Recovery Time	I_F=10A,T_J=25℃ diF/dt=100A/μs	---	8.7	---	ns
Qrr	Reverse Recovery Charge		---	1.95	---	nC

Notes:

1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=12.7A
4.The power dissipation is limited by 150℃ junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics: (T_A=25℃ unless otherwise noted)

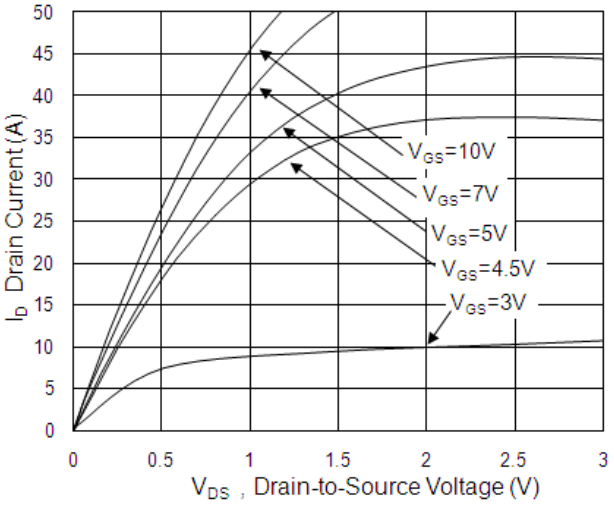


Fig.1 Typical Output Characteristics

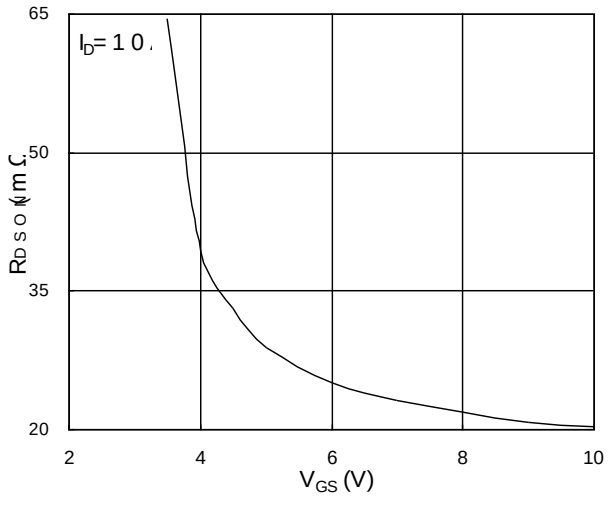


Fig.2 On-Resistance vs. Gate-Source

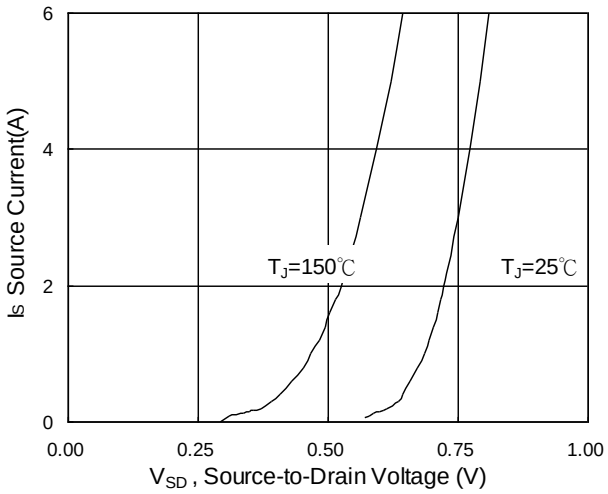


Fig.3 Forward Characteristics Of Reverse

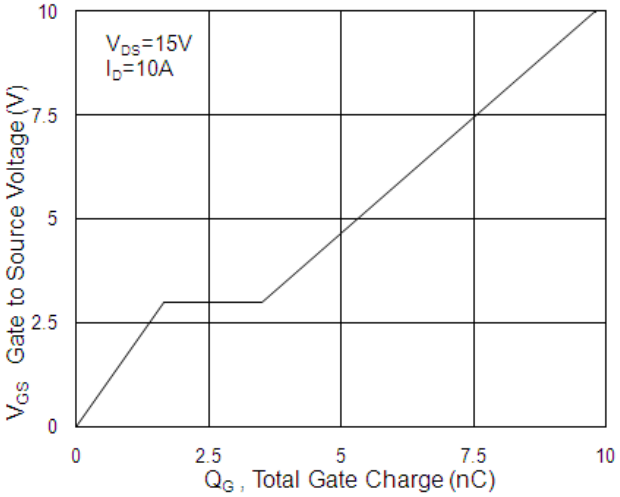


Fig.4 Gate-Charge Characteristics

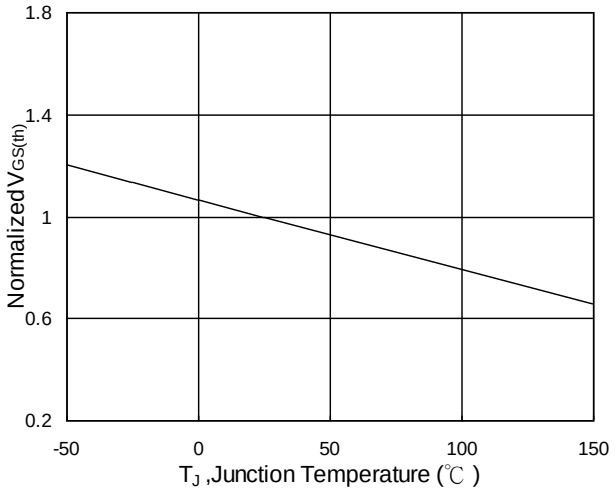


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

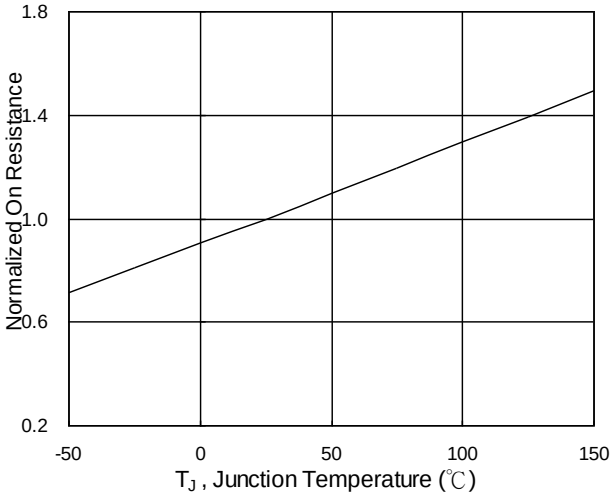


Fig.6 Normalized R_{DSON} vs. T_J

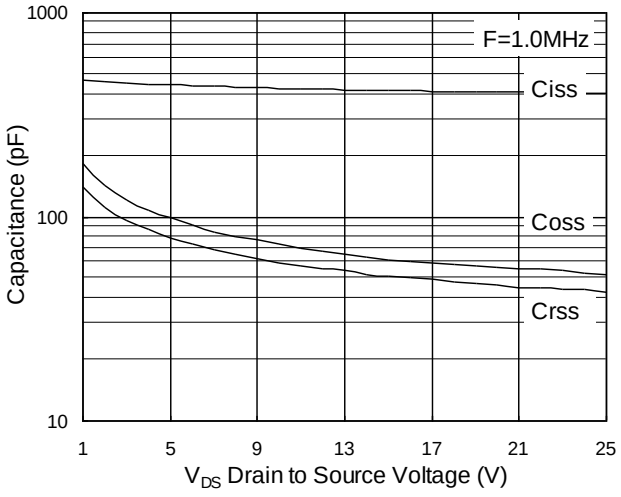


Fig.7 Capacitance

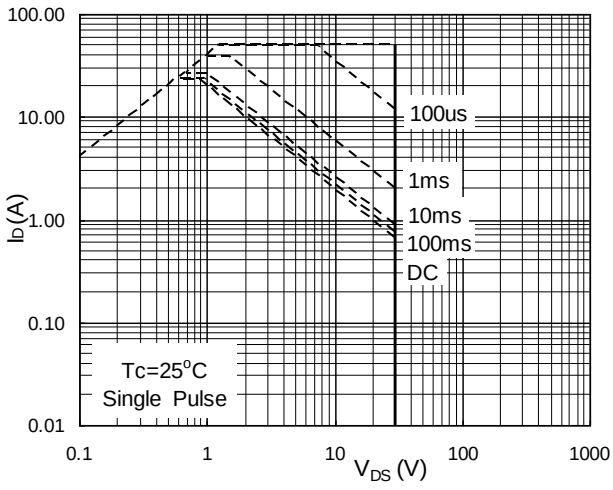


Fig.8 Safe Operating Area

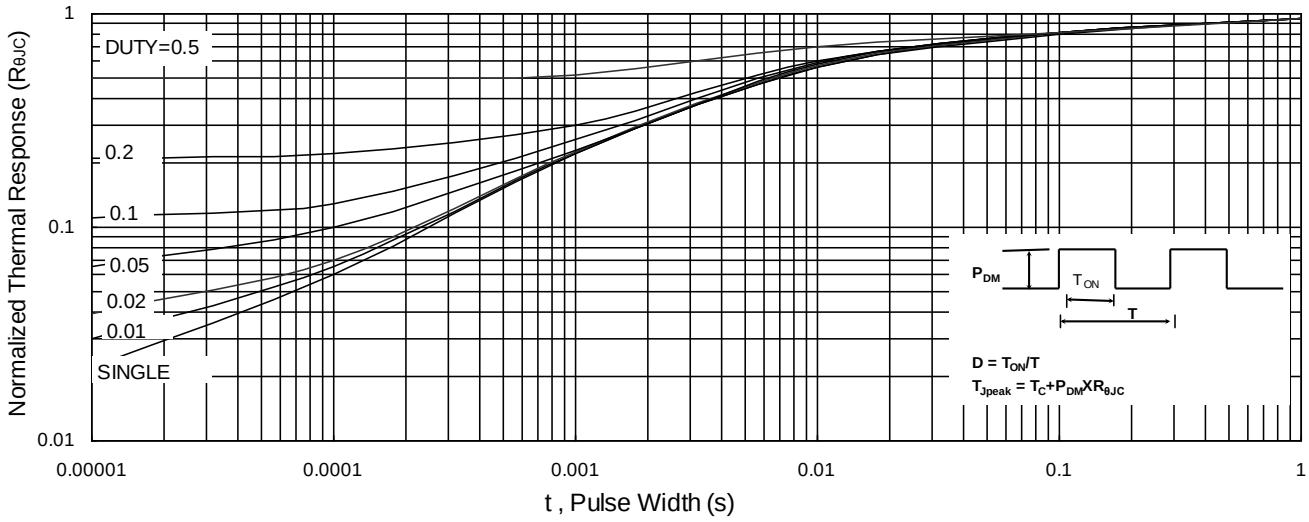


Fig.9 Normalized Maximum Transient Thermal Impedance

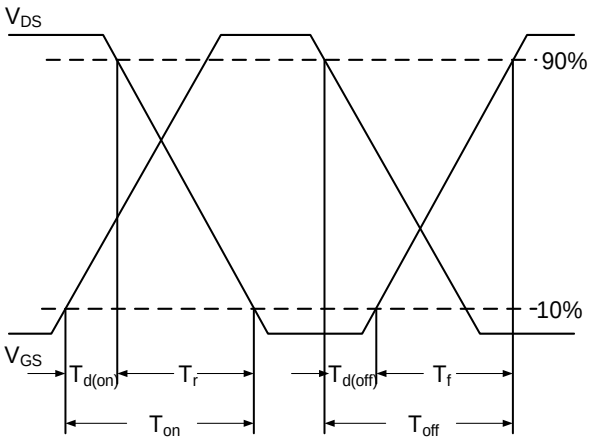


Fig.10 Switching Time Waveform

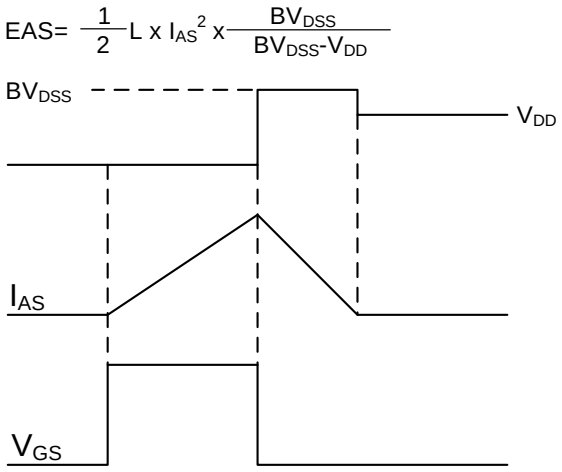


Fig.11 Unclamped Inductive Switching Waveform

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